

Simulation Studies for a GEM-based TPC

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Simulation Studies for a GEM-based TPC

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Simulation Studies

4 Modules:

- 1. Primary ionisation
- 2. Drift of electrons
- 3. Gas amplification with GEMs
- 4. Electronics (shaper, ADC)

Goals: Study influence on the spatial resolution of a TPC of

- Electric and magnetic fields
- GEM settings
- Pad response, pad geometry
- Ion backdrift



Creating Primary Ionisation





Mean number of clusters → Distance between clusters from exponential distribution with this mean value

Probability for number of electrons per cluster → Choose randomly according to distribution

Creating a Track



- Randomly choose distance to next cluster
- Choose # of e^- in this cluster
- 3D information possible
- B fields possible





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Drifting Electrons



Parametrise gas properties simulated with MAGBOLTZ



Dice coordinates after drifting according to longitudinal and transverse diffusion

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Amplification with GEMs (1)



From measurements:

- Parametrisation of charge transfer in triple GEM structure: collection, gain, extraction
- Charge broadening

 only due to diffusion
 between GEMs
 → Simulate diffusion
 with Magboltz



Amplification with GEMs (2)



- Calculate number of secondary e⁻ from charge transfer combined with binomial statistics
- Integrate over 2D gaussian
 with sigma of charge cloud to get charge on pads
 → Voxel information:
 charge on channel c
 at time t



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Electronics: Shaping and ADC



- Determine center of gravity of charge in time
- Apply shaping function (Gaussian at the moment)
- Fill electrons into time bins
- Normalise charge with ADC range
- Integrate charge for every ADC bin





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Inputs for Simulation



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Gain Factor



Mean gain for one GEM from charge transfer parametrisation to high. To match charge spectrum from measurement: Decrease it by factor to account for temperature difference.



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First Comparision to Measurement



$1.27 \times 6.985 \text{ mm}^2$ Pads, TDR Gas, 0T, DESY Testbeam



Conclusion

Advantages:

- Simulation independent from big simulation packages
- Amplification with GEMs (accounts for different settings)
- Magnetic fields and 3D tracks possible
- Many input parameters for systematic studies

Limitation:

No spatial propagation of δ -electrons during primary ionisation

Outlook:

- Verification of simulation with testbeam data
- Systematic studies for ILC TPC